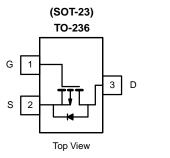
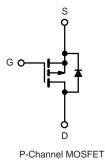


UT2321G-AE3-R-VB Datasheet

P-Channel 30 V (D-S) MOSFET

| PRODUC | CT SUMMARY | | |
|---------------------|------------------------------------|---------------------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) Typ. | I _D (A) ^a | Q _g (Typ.) |
| | 0.046 at V _{GS} = - 10 V | - 5.6 | |
| - 30 | 0.049 at V _{GS} = - 6 V | - 5 | 11.4 nC |
| | 0.054 at V _{GS} = - 4.5 V | -4.5 | |





FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested



APPLICATIONS

- For Mobile Computing
 - Load Switch
 - Notebook Adaptor Switch
 - DC/DC Converter

| Parameter | | Symbol | Limit | Unit |
|--|------------------------|-----------------------------------|----------------------|------|
| Drain-Source Voltage | | V _{DS} | - 30 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | v |
| Continuous Drain Current (T. 450 °C) | T _C = 25 °C | | - 5.6 | |
| | T _C = 70 °C | | - 5.1 | |
| Continuous Drain Current ($T_J = 150 \ ^{\circ}C$) | T _A = 25 °C | I _D | - 5.4 ^{b,c} | |
| | T _A = 70 °C | | - 4.3 ^{b,c} | А |
| Pulsed Drain Current (t = 100 µs) | • | I _{DM} | - 18 | |
| Continuus Source Drain Diade Current | T _C = 25 °C | 1 | - 2.1 | |
| Continous Source-Drain Diode Current | T _A = 25 °C | I _S | - 1 ^{b,c} | |
| | T _C = 25 °C | | 2.5 | |
| Maximum Davida Diasia atian | T _C = 70 °C | | 1.6 | 14/ |
| Maximum Power Dissipation | T _A = 25 °C | P _D | 1.25 ^{b,c} | W |
| | T _A = 70 °C | 1 | 0.8 ^{b,c} | |
| Operating Junction and Storage Temperatur | e Range | T _J , T _{stg} | - 55 to 150 | °C |

THERMAL RESISTANCE RATINGS Parameter Symbol Typical Maximum Unit Maximum Junction-to-Ambient^{b,d} $t \le 5 s$ $\mathsf{R}_{\mathsf{thJA}}$ 75 100 °C/W 40 Maximum Junction-to-Foot (Drain) 50 Steady State $\mathsf{R}_{\mathsf{thJF}}$

Notes:

a. Based on $T_C = 25 \text{ °C}$. b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 166 °C/W.

| SPECIFICATIONS (T _{.1} = 25 °C, | unless othe | rwise noted) | | | | | |
|---|-------------------------|--|-------|-------|-------|--------|--|
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 V, I_D = -250 \mu A$ | - 30 | | | V | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | I _D = - 250 μA | | - 19 | | m\//°C | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | $1D = -220 \mu A$ | | 4 | | mV/°C | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$ | - 0.5 | | - 2.0 | V | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | | ± 100 | nA | |
| Zara Cata Valtaga Drain Current | I | $V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ | | | - 1 | | |
| Zero Gate Voltage Drain Current | IDSS | $V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$ | | | - 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \leq$ - 5 V, V_{GS} = - 10 V | - 2.5 | | | A | |
| | | V _{GS} =- 10 V, I _D = - 4.4 A | | 0.046 | | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} =- 6 V, I _D = - 4 A | | 0.049 | | Ω | |
| | | $V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -3.6 \text{ A}$ | | 0.054 | | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 15 V, I _D = - 3.4 A | | 18 | | S | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | | 1295 | | | |
| Output Capacitance | C _{oss} | V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz | | 150 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 130 | | | |
| Total Gate Charge | Qg | $V_{DS} = -15 \text{ V}, \text{ V}_{GS} = -10 \text{ V}, \text{ I}_{D} = -5.4 \text{ A}$ | | 24 | 36 | | |
| Total Gale Charge | Зg | | | 11.4 | 17 | nC | |
| Gate-Source Charge | Q _{gs} | V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_{D} = - 5.4 A | | 3.4 | | nc | |
| Gate-Drain Charge | Q _{gd} | | | 3.8 | | | |
| Gate Resistance | R _g | f = 1 MHz | 1.5 | 7.7 | 15.4 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 13 | 20 | | |
| Rise Time | t _r | V_{DD} = - 15 V, R_L = 3.5 Ω | | 4 | 8 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_{D}\cong$ - 4.3 A, V_{GEN} = - 10 V, R_{g} = 1 Ω | | 38 | 57 | | |
| Fall Time | t _f | | | 6 | 12 | ns | |
| Turn-On Delay Time | t _{d(on)} | | | 28 | 42 | 115 | |
| Rise Time | t _r | V_{DD} = - 15 V, R_L = 3.5 Ω | | 16 | 24 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong$ - 4.3 A, V_{GEN} = - 4.5 V, R_g = 1 Ω | | 30 | 45 | | |
| Fall Time | t _f | | | 10 | 20 | | |
| Drain-Source Body Diode Characteristic | | | | 1 | | 1 | |
| Continuous Source-Drain Diode Current | ۱ _S | T _C = 25 °C | | | - 2.1 | А | |
| Pulse Diode Forward Current (t = $100 \mu s$) | I _{SM} | | | | - 80 | | |
| Body Diode Voltage | V _{SD} | $I_{S} = -4.3 \text{ A}, V_{GS} = 0 \text{ V}$ | | - 0.8 | - 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | ļ | | 15 | 23 | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = - 4.3 A, dl/dt = 100 A/µs, T ₁ = 25 °C | | 7 | 14 | nC | |
| Reverse Recovery Fall Time | t _a | | | 8 | | ns | |
| Reverse Recovery Rise Time | t _b | | | 7 | | 113 | |

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

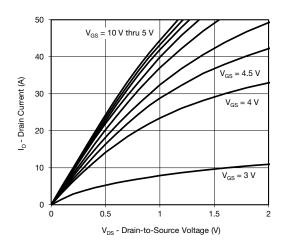
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

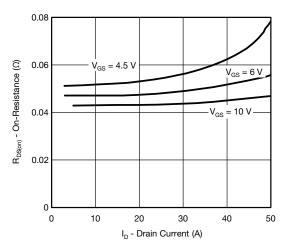




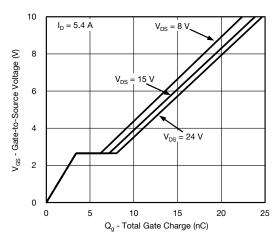




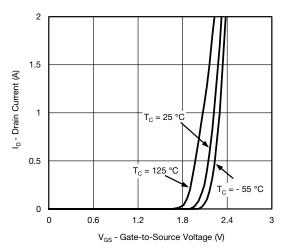
Output Characteristics



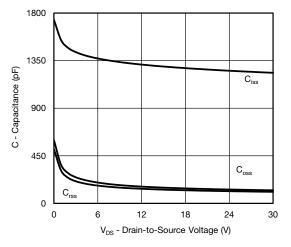
On-Resistance vs. Drain Current



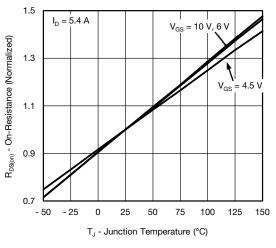
Gate Charge



Transfer Characteristics



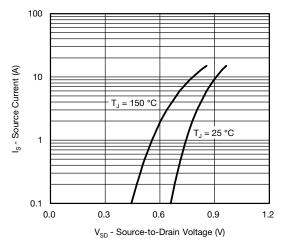
Capacitance



On-Resistance vs. Junction Temperature



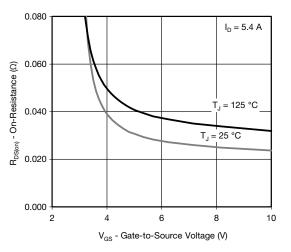
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



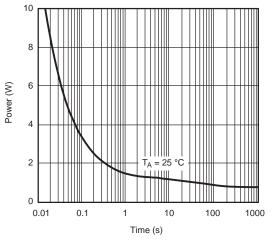
Source-Drain Diode Forward Voltage



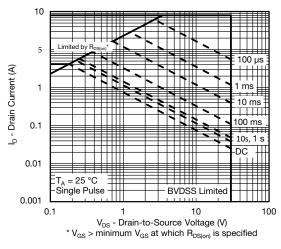
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



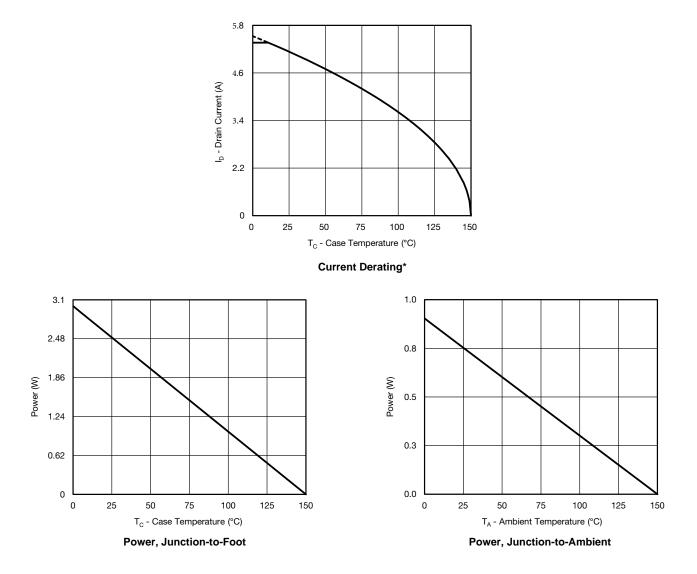
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



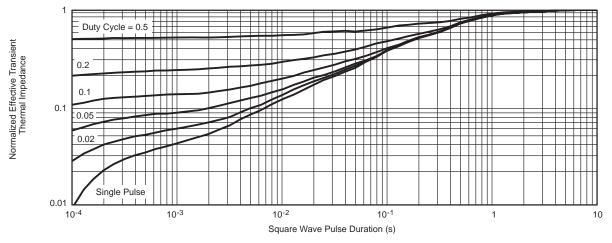
* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







| Max 1.12 0.10 1.02 0.50 0.18 3.04 2.64 1.40 | Min 0.035 0.0004 0.0346 0.014 0.003 0.110 0.083 | Max 0.044 0.004 0.040 0.020 0.007 0.120 0.104 | | |
|---|---|---|--|--|
| 0.10 1.02 0.50 0.18 3.04 2.64 | 0.0004 0.0346 0.014 0.003 0.110 0.083 | 0.004 0.040 0.020 0.007 0.120 | | |
| 1.02 0.50 0.18 3.04 2.64 | 0.0346 0.014 0.003 0.110 0.083 | 0.040 0.020 0.007 0.120 | | |
| 0.50 0.18 3.04 2.64 | 0.014 0.003 0.110 0.083 | 0.020 0.007 0.120 | | |
| 0.18 3.04 2.64 | 0.003 0.110 0.083 | 0.007 0.120 | | |
| 3.04 2.64 | 0.110 0.083 | 0.120 | | |
| 2.64 | 0.083 | | | |
| | | 0.104 | | |
| 1.40 | 0.047 | | | |
| | 0.047 | 0.055 | | |
| 0.95 BSC | 0.037 | 4 Ref | | |
| 1.90 BSC | | 0.0748 Ref | | |
| 0.60 | 0.016 | 0.024 | | |
| 0.64 Ref | 0.025 | 5 Ref | | |
| 0.50 Ref | |) Ref | | |
| 8° | 3° | 8° | | |
| _ | 0.64 Ref 0.50 Ref | 0.64 Ref 0.025 0.50 Ref 0.026 | | |

UT2321G-AE3-R-VB



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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